

## UT2311-F

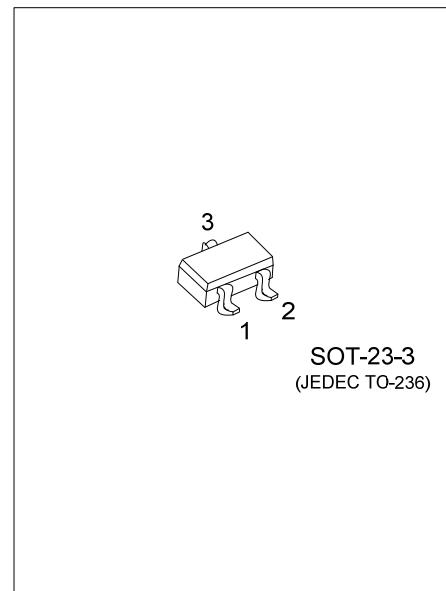
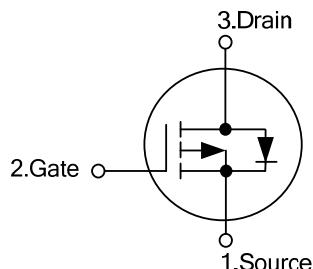
Power MOSFET

-4.7A, -20V P-CHANNEL  
ENHANCEMENT MODE  
POWER MOSFET

## ■ FEATURES

- \* Extremely low on-resistance due to high density cell
- \* Perfect thermal performance and electrical capability with advanced technology of trench process

## ■ SYMBOL



## ■ ORDERING INFORMATION

Ordering Number		Package	Pin Assignment			Packing
Lead Free	Halogen Free		1	2	3	
UT2311L-AE2-R	UT2311G-AE2-R	SOT-23-3	G	S	D	Tape Reel

Note: Pin Assignment: G: Gate S: Source D: Drain

UT2311G-AE2-R 	(1)Packing Type (2)Package Type (3)Green Package	(1) R: Tape Reel (2) AE2: SOT-23-3 (3) G: Halogen Free and Lead Free, L: Lead Free
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## ■ MARKING

Year: K: 2016 (1H)

L: 2016 (2H)

M: 2017 (1H)

N: 2017 (2H)

Week: 01~26 (A~Z)      Lot Code

■ ABSOLUTE MAXIMUM RATINGS ( $T_C = 25^\circ\text{C}$ , unless otherwise noted)

PARAMETER	SYMBOL	RATINGS	UNIT
Drain-Source Voltage	$V_{DSS}$	-20	V
Gate-Source Voltage	$V_{GSS}$	$\pm 8$	V
Continuous Drain Current	$I_D$	-4.7	A
Pulsed Drain Current	$I_{DM}$	-18.8	A
Power Dissipation ( $T_C=25^\circ\text{C}$ ) (Note 2)	$P_D$	1.25	W
Junction Temperature	$T_J$	+150	$^\circ\text{C}$
Storage Temperature	$T_{STG}$	-55 ~ +150	$^\circ\text{C}$

Notes: 1. Absolute maximum ratings are those values beyond which the device could be permanently damaged.

Absolute maximum ratings are stress ratings only and functional device operation is not implied.

2. Surface mounted on 1 in 2 copper pad of FR4 board.

■ THERMAL CHARACTERISTICS

PARAMETER	SYMBOL	RATINGS	UNIT
Junction to Ambient (PCB mounted)	$\theta_{JA}$	80	$^\circ\text{C}/\text{W}$

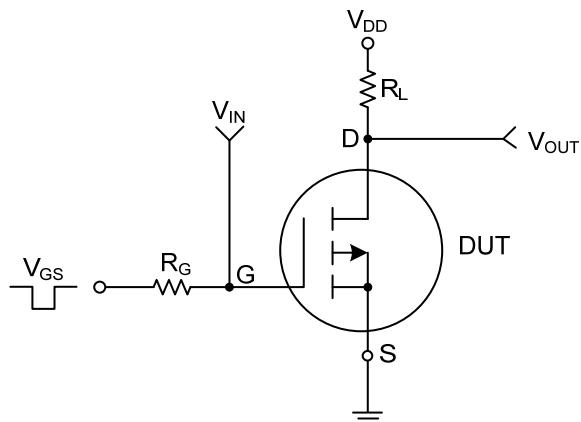
Note: Surface Mounted on FR4 board  $t \leq 5$  sec.

■ ELECTRICAL CHARACTERISTICS ( $T_A = 25^\circ\text{C}$ , unless otherwise specified)

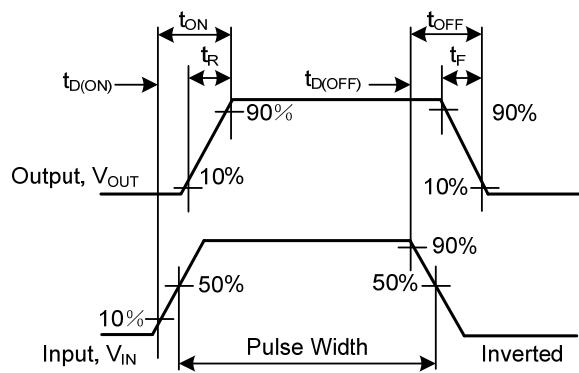
PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
<b>OFF CHARACTERISTICS</b>						
Drain-Source Breakdown Voltage	$BV_{DSS}$	$V_{GS} = 0\text{V}, I_D = -250\mu\text{A}$	-20			V
Drain-Source Leakage Current	$I_{DSS}$	$V_{DS} = -16\text{V}, V_{GS} = 0\text{V}$			-1.0	$\mu\text{A}$
Gate-Source Leakage Current	$I_{GSS}$	$V_{GS} = \pm 8\text{V}, V_{DS} = 0\text{V}$			$\pm 100$	nA
Breakdown Voltage Temperature Coefficient	$\Delta BV_{DSS}/\Delta T_J$	Reference to $25^\circ\text{C}$ , $I_D = -1\text{mA}$		-0.02		$\text{V}/^\circ\text{C}$
<b>ON CHARACTERISTICS</b>						
Gate Threshold Voltage	$V_{GS(TH)}$	$V_{DS} = V_{GS}, I_D = -250\mu\text{A}$	-0.3		-0.8	V
Static Drain-Source On-State Resistance	$R_{DS(ON)}$	$V_{GS} = -4.5\text{V}, I_D = -4.0\text{ A}$			55	$\text{m}\Omega$
		$V_{GS} = -2.5\text{V}, I_D = -2.5\text{ A}$			85	$\text{m}\Omega$
		$V_{GS} = -1.8\text{V}, I_D = -1.0\text{ A}$			100	$\text{m}\Omega$
<b>DYNAMIC PARAMETERS<sup>b</sup></b>						
Input Capacitance	$C_{ISS}$	$V_{DS} = -10\text{V}, V_{GS} = 0\text{V}, f = 1.0\text{MHz}$		850		pF
Output Capacitance	$C_{OSS}$			70		pF
Reverse Transfer Capacitance	$C_{RSS}$			55		pF
<b>SWITCHING PARAMETERS<sup>b</sup></b>						
Total Gate Charge	$Q_G$	$V_{GS} = -10\text{V}, V_{GS} = -4.5\text{V}, I_D = -3.0\text{A}$		9.6		nC
Gate Source Charge	$Q_{GS}$			1.6		nC
Gate Drain Charge	$Q_{GD}$			2.0		nC
Turn-ON Delay Time	$t_{D(ON)}$	$V_{DD} = -10\text{V}, V_{GS} = -4.5\text{V}, I_D = -1.0\text{A}$ $R_G = 25\Omega$		6.0		ns
Turn-ON Rise Time	$t_R$			21.6		ns
Turn-OFF Delay Time	$t_{D(OFF)}$			51		ns
Turn-OFF Fall-Time	$t_F$			13.8		ns
<b>SOURCE- DRAIN DIODE RATINGS AND CHARACTERISTICS</b>						
Maximum Body-Diode Continuous Current	$I_S$	$V_G = V_D = 0\text{V}$ , Force Current			-4.7	A
Maximum Body-Diode Pulsed Current	$I_{SM}$				-18.8	A
Drain-Source Diode Forward Voltage	$V_{SD}$	$I_S = -1.0\text{A}, V_{GS} = 0\text{V}, T_J = 25^\circ\text{C}$			-1.0	V

Note: Pulse test; pulse width  $\leq 300\mu\text{s}$ , duty cycle  $\leq 2\%$ .

## ■ TEST CIRCUITS AND WAVEFORMS



Switching Test Circuit



Switching Waveforms

■ TYPICAL CHARACTERISTICS

Fig.1 Continuous Drain Current vs. Case Temperature

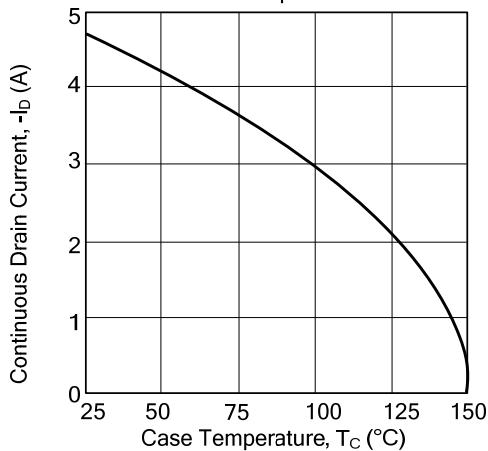


Fig.2 Normalized R<sub>DSON</sub> vs. Junction Temperature

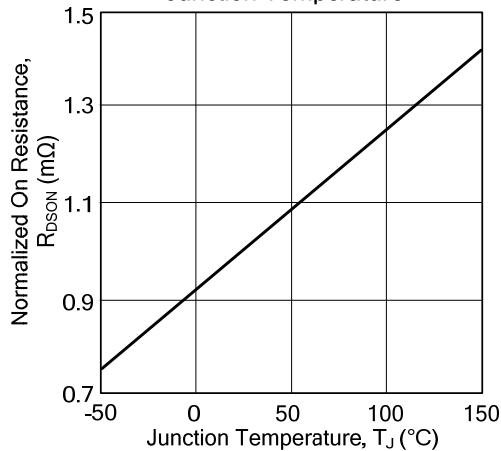


Fig.3 Normalized V<sub>th</sub> vs. Junction Temperature

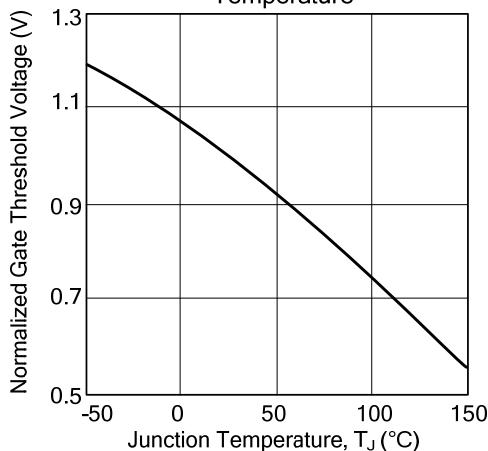


Fig.4 Gate Charge Waveform

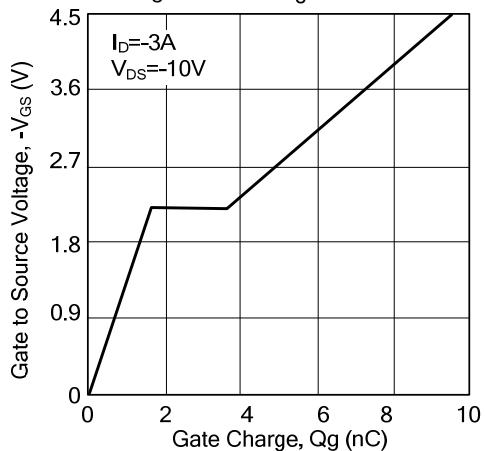


Fig.5 Normalized Transient Impedance

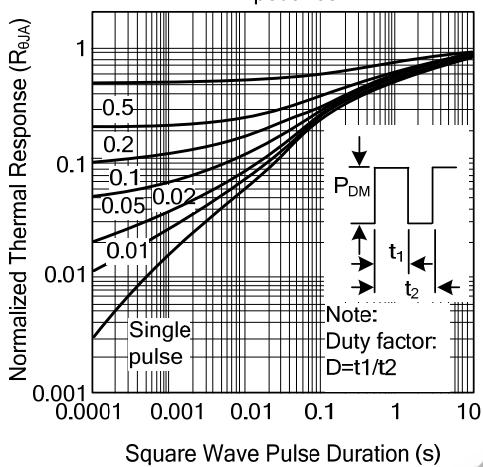
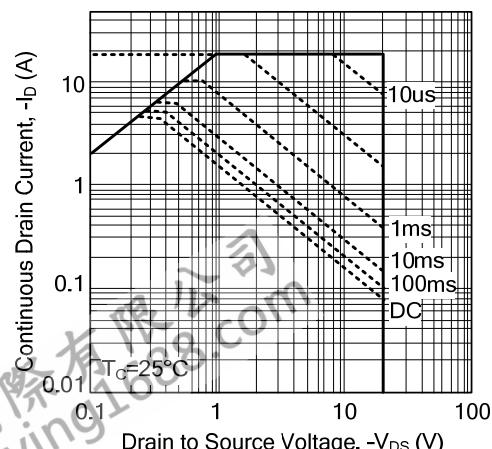


Fig.6 Maximum Safe Operation Area



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